

Features:

- High speed switching
- Voltage drive
- Low inductance module structure

Typical Applications:

- Inverter for Motor Drive
- Inverter welding machines
- Uninterruptible Power Supply
- Industrial machines

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | VALUE | | | UNIT |
|----------------------|--|--|-------|------|------|------|
| | | | Min. | Typ. | Max. | |
| V _{CES} | Collector-Emitter voltage | T _j =25°C | | | 1250 | V |
| V _{GES} | Gate-Emitter voltage | T _j =25°C | | | ±30 | V |
| I _C | Collector current | Continuous@ T _C =100°C | | | 100 | A |
| I _{CP} | | t _p =1ms | | | 200 | A |
| P _C | Collector power dissipation | T _C =25°C ,1 device | | | 500 | W |
| T _j | Junction temperature | / | | | 175 | °C |
| T _{vj(op)} | Temperature under switching conditions | T _{vj op} > 150°C is only allowed for operation at overload conditions. | -40 | | 175 | °C |
| T _{stg} | Storage temperature | / | -40 | | 125 | °C |
| V _{iso} | Isolation between terminal and copper base | T _j =25°C ,AC: 1minute | 2500 | | | V |
| Screw torque | Mounting(M6) | / | 3.5 | | 5.0 | N·m |
| | Terminals(M5) | / | 2.4 | | 3.0 | N·m |
| I _{CES} | Zero gate voltage collector current | T _j =25°C ,V _{CE} =1200V, V _{GE} =0V | | | 1 | mA |
| I _{GES} | Gate-Emitter leakage current | T _j =25°C ,V _{CE} =0V, V _{GE} =±20V | | | ±2 | µA |
| V _{GE(th)} | Gate-Emitter threshold voltage | T _j =25°C ,V _{CE} =20V, I _C =100mA | 5 | | 8.5 | V |
| V _{CE(sat)} | Collector-Emitter saturation voltage | T _j =25°C ,V _{GE} =15V, I _C =100A | | 1.75 | 2.40 | V |
| | | T _j =125°C ,V _{GE} =15V, I _C =100A | | 1.95 | | V |
| | | T _j =150°C ,V _{GE} =15V, I _C =100A | | 2.05 | | V |
| C _{ies} | Input capacitance | T _j =25°C ,V _{CE} =10V, V _{GE} =0V, f=1MHz | | 9.1 | | nF |
| t _{on} | Turn-on time | T _j =150°C ,V _{CC} =600V, I _C =100A, V _{GE} =±15V, R _G =10Ω, Inductive load | | 160 | | ns |
| t _r | | | | 40 | | ns |
| t _{off} | | | | 600 | | ns |
| t _f | | | | 200 | | ns |
| tsc | Short Circuit Withstand Time | T _j =150°C ,V _{CC} =720V, V _{GE} =±15V, R _G =10Ω | 10 | | | µs |
| V _F | Forward on voltage | T _j =25°C ,I _F =100A | | 1.80 | 2.6 | V |
| | | T _j =125°C ,I _F =100A | | 1.88 | | V |
| | | T _j =150°C ,I _F =100A | | 1.95 | | V |
| t _{rr} | Reverse recovery time | T _j =125°C ,I _F =100A | | 135 | | ns |
| | | T _j =150°C ,I _F =100A | | 150 | | ns |
| R _{th(j-c)} | Thermal resistance(1 device) | IGBT | | | 0.30 | °C/W |
| | | FWD | | | 0.50 | °C/W |
| R _{th(c-f)} | Contact thermal resistance (1 device) | With thermal compound | | 0.05 | | °C/W |
| W _t | Weight | | | | 155 | g |
| Outline | M38 | | | | | |

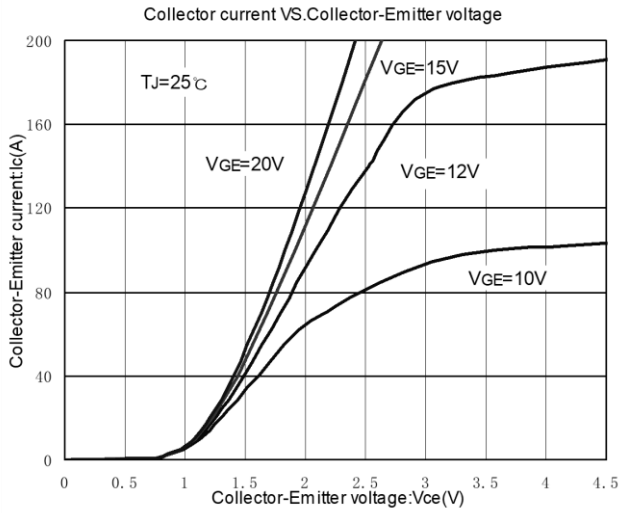


Fig.1

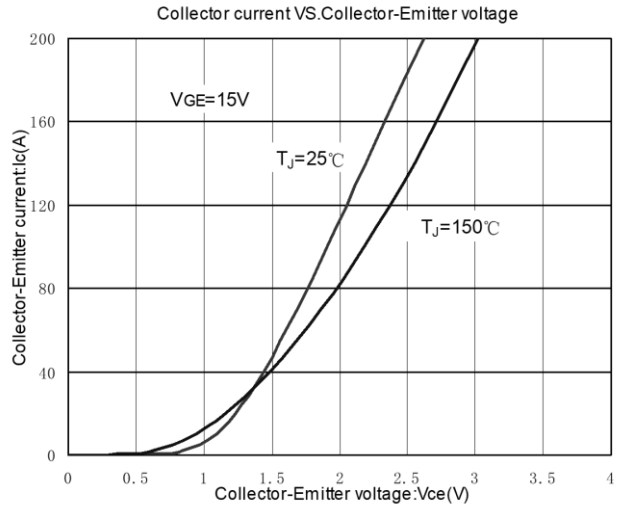


Fig.2

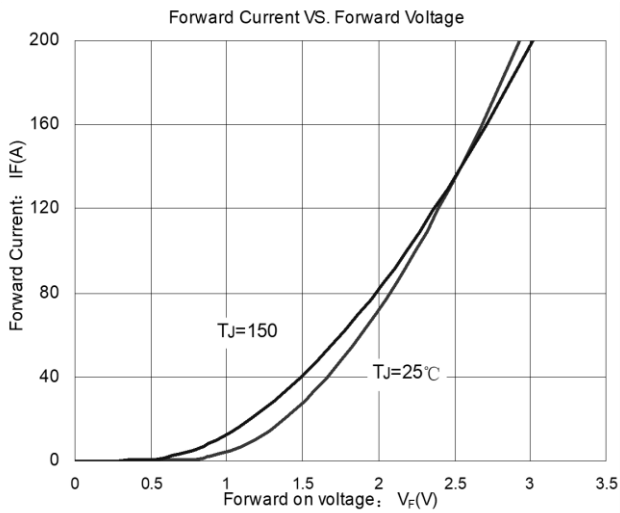


Fig.3

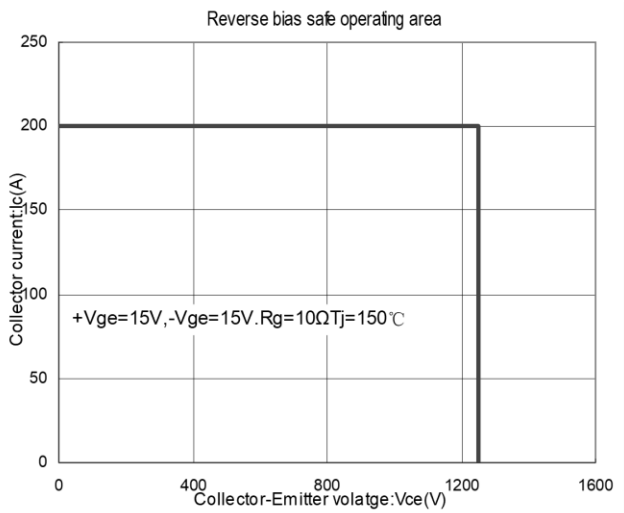


Fig.4

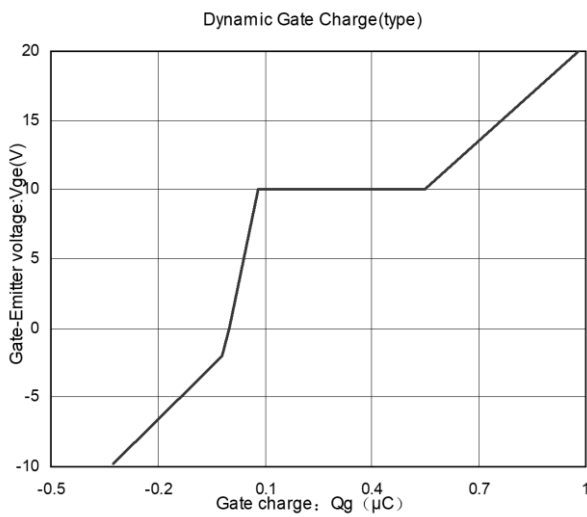


Fig.5

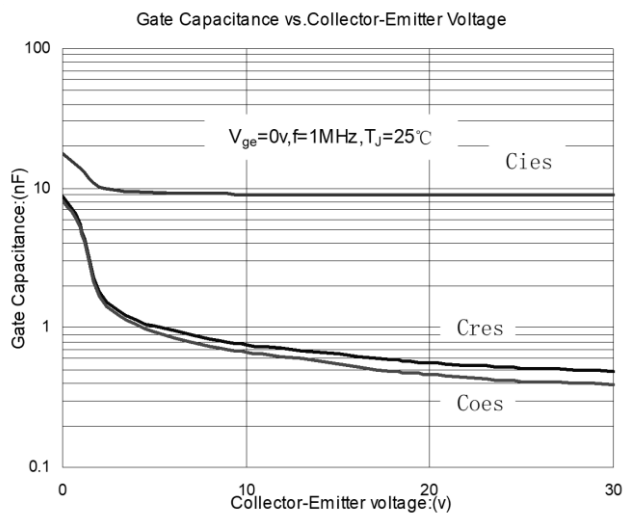


Fig.6

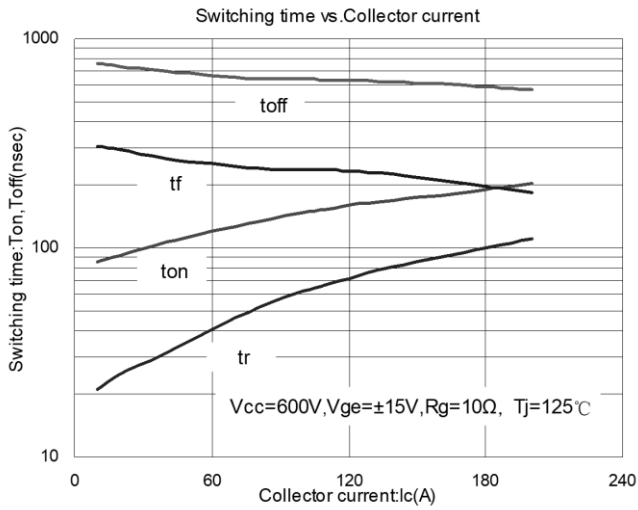


Fig.7

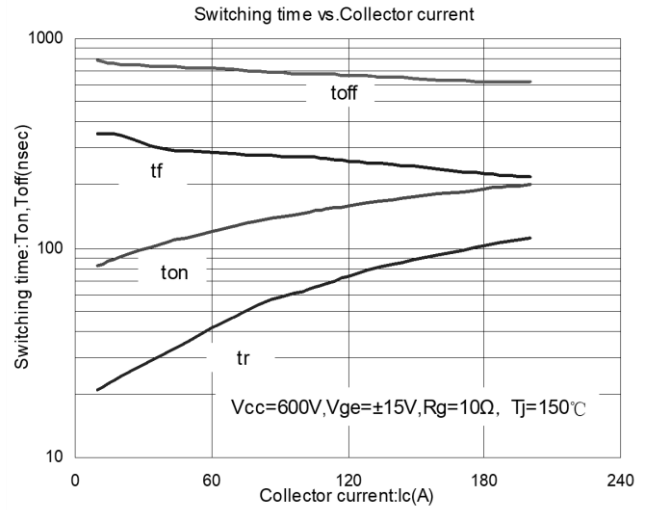


Fig.8

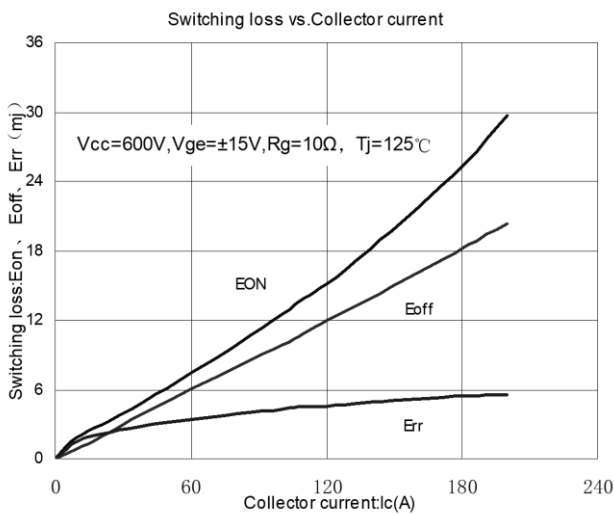


Fig.9

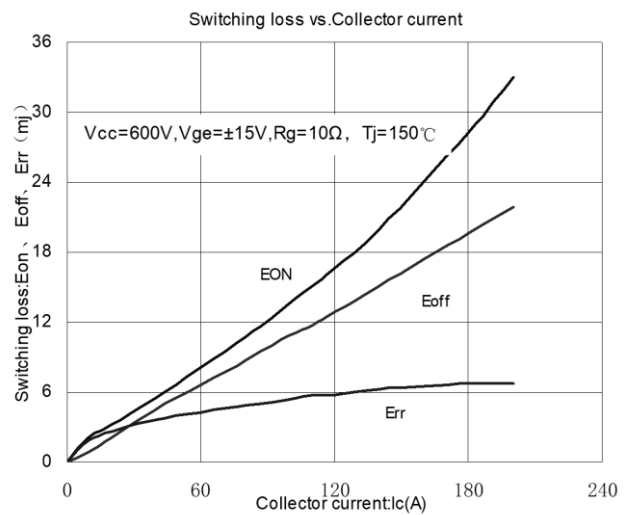


Fig.10

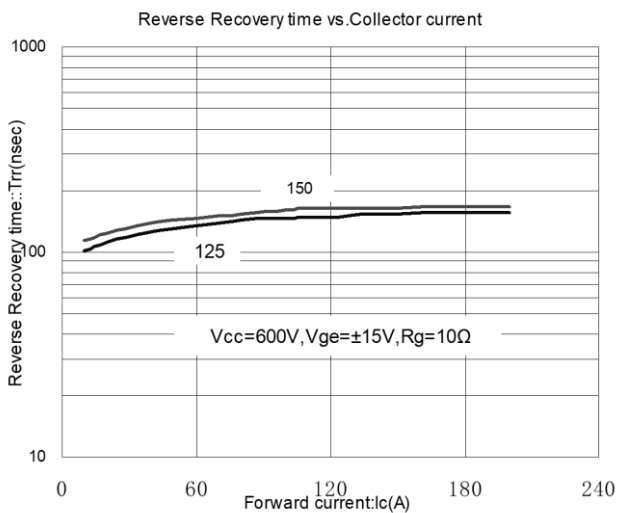


Fig.11

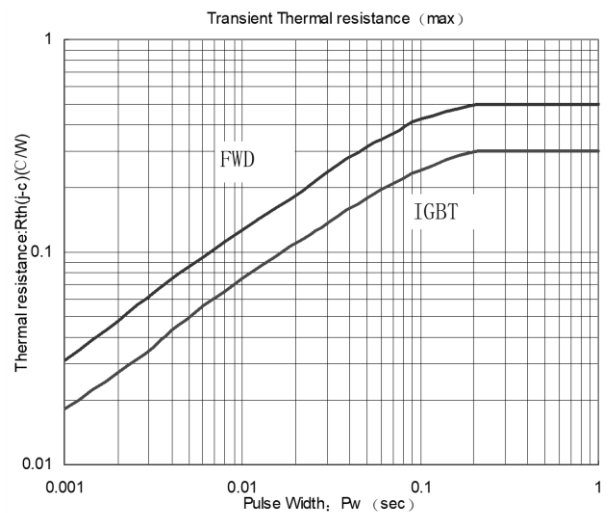
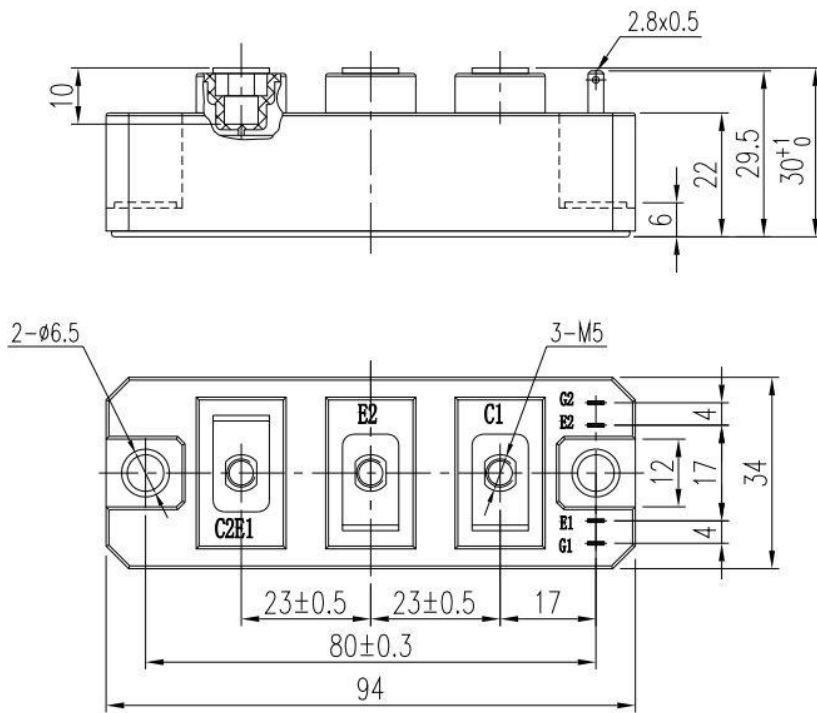
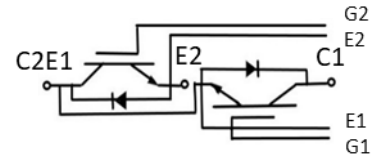


Fig.12



MD100MB120S



Unmarked dimensional tolerance: $\pm 0.5\text{mm}$